

## TO-251-3L Plastic-Encapsulate Transistors

**B772** TRANSISTOR (PNP)

### FEATURES

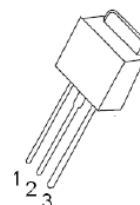
- Low Speed Switching

### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
I <sub>C</sub>	Collector Current -Continuous	-3	A
P <sub>C</sub>	Collector Power Dissipation	1.25	W
R <sub>θJA</sub>	Thermal Resistance, junction to Ambient	100	°C/W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

### TO-251-3L

1. EMITTER
2. COLLECTOR
3. BASE



### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-30			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -100μA, I <sub>C</sub> =0	-6			V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -40V, I <sub>E</sub> =0			-1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =-30V, I <sub>B</sub> =0			-10	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-6V, I <sub>C</sub> =0			-1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> = -1A	60		400	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-2A, I <sub>B</sub> = -0.2A			-0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-2A, I <sub>B</sub> = -0.2A			-1.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> =-0.1A f =10MHz	50	80		MHz

### CLASSIFICATION OF h<sub>FE</sub>

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400